



SKJ10N80B

N-Channel Multi-EPI Super-J MOSFET

Features

- $BV_{DSS} \geq 800V$
- $I_D = 10A$
- $R_{DS(on)} \leq 500m\Omega @ V_{GS}=10V$

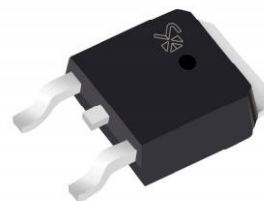
$BV_{DSS}, T_A=25^\circ C$	$I_D, T_A=25^\circ C$	$R_{DS(on)}, typ@10V$
800 V	10A	410m Ω

Application

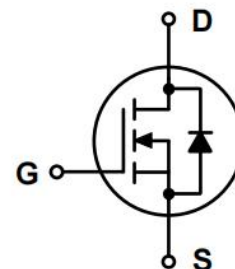
- Power switching application
- Hard Switched and High Frequency Circuits
- Uninterruptible Power Supply

Description

- Proprietary New Planar Technology
- High Reliability Capability



TO-252



Absolute Maximum Ratings($T_C=25^\circ C$, unless otherwise noted.)

Parameter	Symbol	Value	Unit
Drain-source Voltage	V_{DS}	800	V
Gate-source Voltage	V_{GS}	± 30	V
Drain Current-Continuous	I_D	10	A
Operating Junction Temperature Range	T_J	-55~150	$^\circ C$
Storage Temperature Range	T_{STG}	-55~150	$^\circ C$

Electrical Characteristics($T_J=25^\circ C$, unless otherwise noted.)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-source Breakdown voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	800			V
Gate Voltage Drain Current	I_{DSS}	$V_{DS}=800V, V_{GS}=0V$			1	μA
Gate-source leakage current	I_{GSS}	$V_{GS}=\pm 30V, V_{DS}=0V$			± 100	nA
Gate Threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.5	3.5	4.5	V
Static Drain to Source on resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=5A$		410	500	m Ω
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_{SD}=10A$			1.4	V

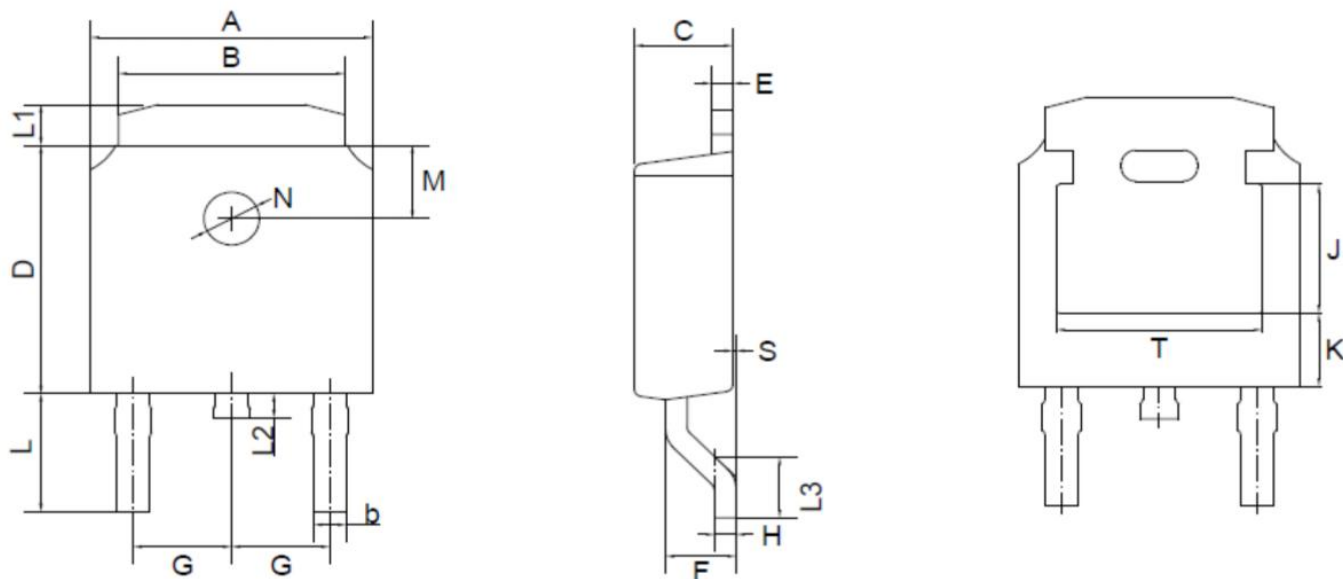


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Package Information

TO-252

Dimensions in mm



TO-252(D-PAK) mechanical data

UNIT		A	B	b	C	D	E	F	G	H	L	L1	L2	L3	S	M	N	J	K	T
mm	max	6.7	5.5	0.8	2.5	6.3	0.6	1.8	2.29	0.55	3.1	1.2	1.0	1.75	0.1	1.8	1.3	3.16	1.80	4.83
	min	6.3	5.1	0.3	2.1	5.9	0.4	1.3	TYPICAL	0.45	2.7	0.8	0.6	1.40	0.0	TYPICAL	TYPICAL	ref.	ref.	ref.
mil	max	264	217	31	98	248	24	71	90	22	122	47	39	69	4	71	51	124	71	190
	min	248	201	12	83	232	16	51	TYPICAL	18	106	31	24	55	0	TYPICAL	TYPICAL	ref.	ref.	ref.